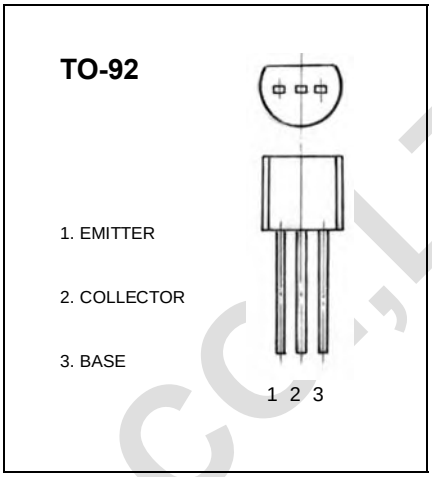
BF421
BF423

TRANSISTOR (PNP)



FEATURES

Power dissipation

P_{CM}: 0.83 W (Tamb=25℃)

Collector current

I_{CM}: -100 mA

Collector-base voltage

$V_{(BR)CBO}$: BF421 -300 V
BF423 -250 V

Operating and storage junction temperature range

T_J, T_{stg}: -55 to +150

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage BF421 BF423	V_{CBO}	Ic=-100μA , I_E=0	-300 -250			V
Collector-emitter breakdown voltage BF421 BF423	V_{CEO}	I_C= -1mA , I_B=0	-300 -250			V
Emitter-base breakdown voltage	V_{EBO}	I_E=-100μA, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-200V, I_E=0			-0.01	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-5V, I_C=0			-0.05	μA
DC current gain	h_{FE}	V_{CE}=-20V, I_C=-25mA	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-30 mA, I_B=- 5mA			-0.6	V
Transition frequency	f_T	V_{CE}=-10V, I_C= -10mA	60			MHz